

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-42. (Cancelled)

43. (New) A dynamic random access memory comprising:

a substrate;

an insulating film over the substrate;

at least one word line;

at least one bit line intersecting perpendicularly to the word line;

a crystalline semiconductor film comprising silicon at an intersection of the word line and the bit line, formed on the insulating film;

an interlayer insulating film on the crystalline semiconductor film; and

an electrode over a drain region of the crystalline semiconductor film with the interlayer insulating film interposed therebetween,

wherein the insulating film has at least one asperity of less than 30Å in height on the upper surface thereof.

44. (New) A dynamic random access memory according to claim 43, wherein the dynamic random access memory further comprises a gate insulating film on the crystalline semiconductor film and a gate electrode on the gate insulating film.

45. (New) A dynamic random access memory according to claim 43, wherein the insulating film comprises silicon oxide.

46. (New) An electronic appliance comprising the dynamic random access memory according to claim 43, wherein the electronic appliance is selected from the group consisting of a TV camera, a head-mount display, a car navigation, a projection display, a video camera, a personal computer, and a cellular telephone.